

ABSOLUTEMAXIMUMRATINGS
(25°C unless otherwise specified)

Storage Temperature	-55°C to +125°C
Operating Temperature	-30°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUTDIODE

Forward Current	±50mA
Power Dissipation	70mW

OUTPUTTRANSISTOR

Collector-emitter Voltage BV _{CEO}	55V
Emitter-collector Voltage BV _{ECO}	6V
Collector Current	50mA
Power Dissipation	150mW

POWERDISSIPATION

Total Power Dissipation	200mW
(derate linearly 2.67mW/°C above 25°C)	

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V _F)	1.0	1.15	1.3	V	I _F = ± 10mA
Output	Collector-emitter Breakdown (BV _{CEO}) (Note 2)	55			V	I _C = 0.5mA
	Emitter-collector Breakdown (BV _{ECO})	6		100	V nA	I _E = 100µA V _{CE} = 20V
Coupled	Current Transfer Ratio (CTR) (Note 2) ISP620-1, ISP620-2, ISP620-4	50		600	%	± 5mA I _F , 5V V _{CE}
	CTR selection available GB	100 30		600	% %	± 5mA I _F , 5V V _{CE} ± 1mA I _F , 0.4V V _{CE}
	Collector-emitter Saturation Voltage V _{CE(SAT)} GB		0.4	0.4	V V	± 8mA I _F , 2.4mA I _C ± 1mA I _F , 0.2mA I _C
	Input to Output Isolation Voltage V _{ISO}	5300 7500			V _{RMS} V _{PK}	See note 1 See note 1
	Input-output Isolation Resistance R _{ISO}	5x10 ¹⁰			Ω	V _{IO} = 500V (note 1)
	Rise Time, tr		4		µs	V _{CE} = 2V,
	Fall Time, tf		3		µs	I _C = 2mA, R _L = 100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

